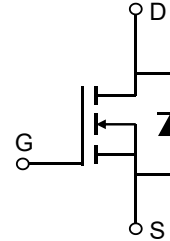


Description

Features

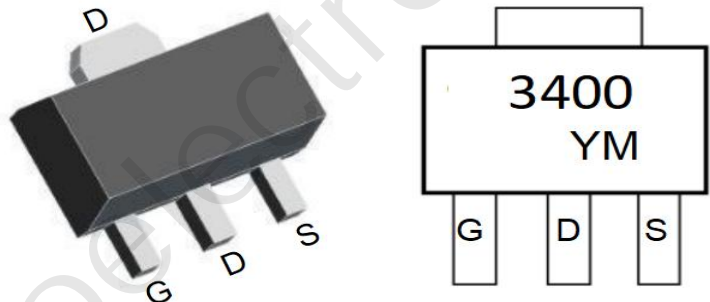
- 30V, 6.5A
- $R_{DS(ON)}$ Typ = 16.6mΩ @ $V_{GS} = 10V$
- $R_{DS(ON)}$ Typ = 18mΩ @ $V_{GS} = 4.5V$
- $R_{DS(ON)}$ Typ = 24mΩ @ $V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMNTU3400A	3400	SOT-89-3L	TAPING	7"	1000	32000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	±12	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	6.5
		$T_A = 100^\circ\text{C}$	3.9
I_{DM}	Pulsed Drain Current ⁽¹⁾	26	A
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	1.6
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾	80	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 12\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	0.5	0.9	1.3	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 10\text{V}$, $I_D = 3.5\text{A}$	-	16.6	21.6	mΩ
		$V_{GS} = 4.5\text{V}$, $I_D = 3\text{A}$	-	18	23.4	mΩ
		$V_{GS} = 2.5\text{V}$, $I_D = 2.5\text{A}$	-	24	31.2	mΩ

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 15\text{V}$, $f = 1\text{MHz}$	-	816	-	pF
C_{oss}	Output Capacitance		-	60	-	pF
C_{rss}	Reverse Transfer Capacitance		-	50	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0$ to 10V $V_{DS} = 15\text{V}$, $I_D = 3\text{A}$	-	19	-	nC
Q_{gs}	Gate Source Charge		-	2	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	2.1	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}$, $V_{DD} = 15\text{V}$ $I_D = 3\text{A}$, $R_{GEN} = 3\Omega$	-	4	-	ns
t_r	Turn-On Rise Time		-	11	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	24	-	ns
t_f	Turn-Off Fall Time		-	2	-	ns

Drain-Source Diode Characteristics and Max Ratings

I_S	Maximum Continuous Drain to Source Diode Forward Current	$V_{GS} = 0\text{V}$, $I_S = 3.5\text{A}$ $I_F = 3\text{A}$, $di/dt = 100\text{A/us}$	-	-	6.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	26	A
V_{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time		-	8.4	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	3.3	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

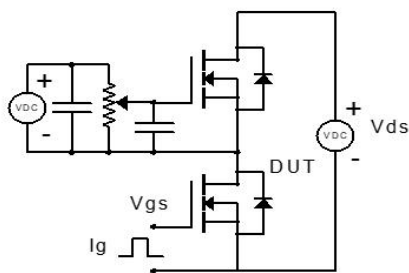


Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

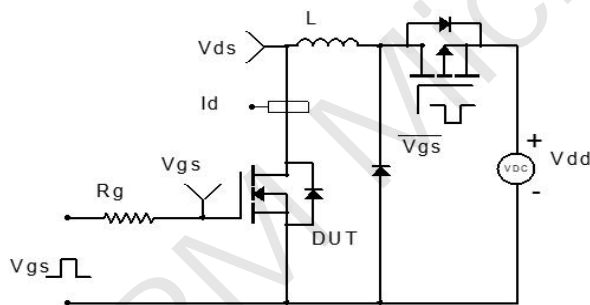


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

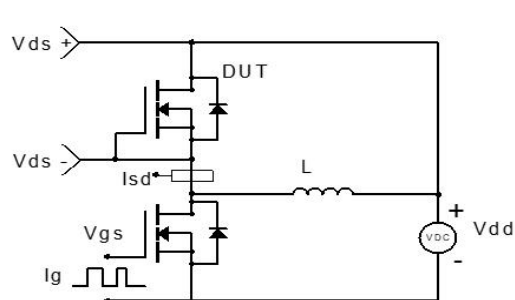
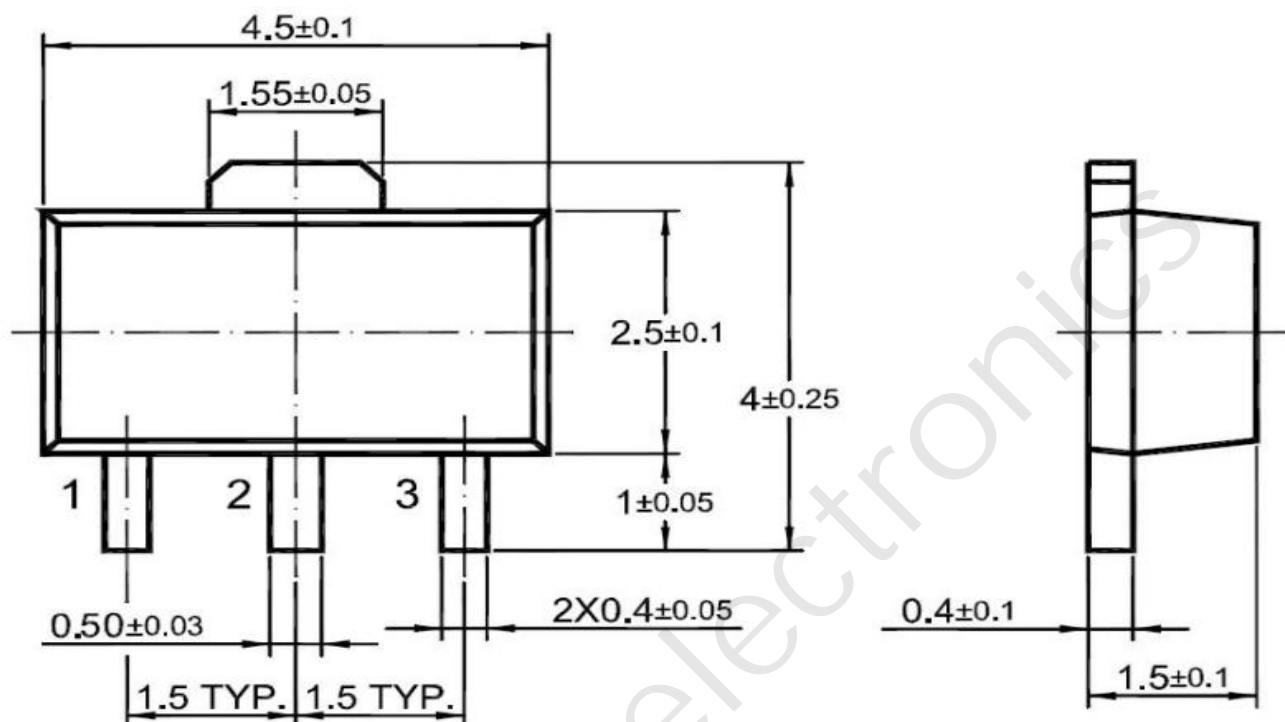


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOP-89-3L)



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